Supporting Information

## Yb-Doped SnO<sub>2</sub> Electron Transfer Layer Assisting the Fabrication of High-Efficiency and Stable Perovskite Solar Cells in Air

Dixin Liu,<sup>a,‡</sup> WenYuan Zhang,<sup>a,‡</sup> Xin Li<sup>*a*,\*</sup>, Ziqiu Ren<sup>*b*,\*</sup>

<sup>a</sup>MIIT Key Laboratory of Critical Materials Technology for New Energy Conversion and Storage, School of Chemistry and Chemical Engineering, State Key Lab of Urban Water Resource and Environment, Harbin Institute of Technology, 150001 Harbin, China <sup>b</sup> Henan Institute of Advanced Technology, Zhengzhou University, Zhengzhou 450052, P.R. China ‡These authors contributed equally to this work. \*Corresponding author: Xin Li, Ziqiu Ren

E-mail address: lixin@hit.edu.cn (X. Li), renziqiu@hit.edu.cn (Z. Ren)

Table S1	Work	function	of SnO <sub>2</sub>	and Yb-	doped S	SnO <sub>2</sub> film
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	SnO <sub>2</sub>	Yb-doped SnO <sub>2</sub>	HOPG <sup>a</sup>
Surface potential (mV)	-370.21	-477.69	1.040
$\Delta SP^{b}(mV)$	-369.17	-476.56	/
Work Function <sup>°</sup> (eV)	4.28	4.17	4.65

<sup>a</sup> HOPG (highly oriented pyrolytic graphite) was used as a reference work function of 4.65eV given by supplier;

- <sup>b</sup>  $\triangle$ SP = SP(samples)-SP(HOPG);
- <sup>c</sup> Work Function =  $e \triangle SP + 4.65 eV$ .

Туре	Jsc	Voc	FF	PCE			
	(mA cm <sup>-2</sup> )	(V)	(%)	(%)			
SnO <sub>2</sub> device	19.12±1.49	0.98±0.04	67.14±4.48	12.63±0.91			
Yb-doped SnO <sub>2</sub> device	$20.24 \pm 0.70$	$1.01 \pm 0.02$	$72.60 \pm 2.51$	$14.92 \pm 0.50$			

**Table S2** Device performance of  $SnO_2$  and Yb-doped  $SnO_2$  perovskite solar cells. The parameters are obtained from the average of 30 devices.



Fig. S1. Voc histograms of PSCs



Fig. S2. Jsc histograms of PSCs



Fig. S3. Fill factor histograms of PSCs



Fig. S4. Long term stability tests of control and optimized devices.